74LVC2G86-Q100

Dual 2-input EXCLUSIVE-OR gate

Rev. 1 — 7 May 2013

Product data sheet

1. General description

The 74LVC2G86-Q100 provides a dual 2-input EXCLUSIVE-OR gate.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant inputs for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - ♦ HBM JESD22-A114F exceeds 2000 V
 - ♦ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- \pm 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low-power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options



3. Ordering information

Table 1. Ordering information

Type number	Package	Package								
	Temperature range	Name	Description	Version						
74LVC2G86DP-Q100	-40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2						
74LVC2G86DC-Q100	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1						

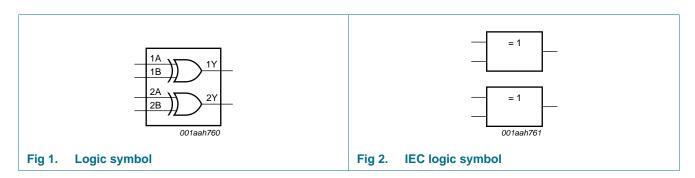
4. Marking

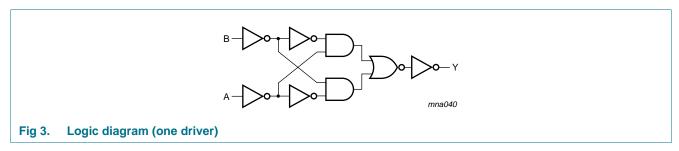
Table 2. Marking codes

Type number	Marking code ^[1]
74LVC2G86DP-Q100	V86
74LVC2G86DC-Q100	V86

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

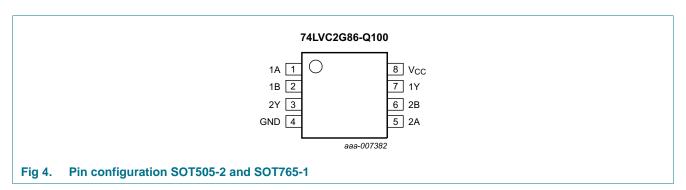
5. Functional diagram





6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table[1]

Input	Output	
nA	nB	nY
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

^[1] H = HIGH voltage level; L = LOW voltage level

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> -0.5	+6.5	V
I _{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0 V$	-	±50	mA
Vo	output voltage	Active mode	[1][2] -0.5	$V_{CC} + 0.5$	V
		Power-down mode	[1][2] -0.5	+6.5	V
Io	output current	$V_O = 0$ to V_{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[3] _	300	mW
T _{stg}	storage temperature		-65	+150	°C

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		1.65	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	Active mode	0	V_{CC}	V
		V _{CC} = 0 V; Power-down mode	0	5.5	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V _{CC} = 1.65 V to 2.7 V	-	20	ns/V
		V _{CC} = 2.7 V to 5.5 V	-	10	ns/V

^[2] When $V_{CC} = 0 \text{ V}$ (Power-down mode), the output voltage can be 5.5 V in normal operation.

^[3] For TSSOP8 packages: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K. For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K.

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

	· · ·	, 0	<u> </u>			
Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
$T_{amb} = -4$	40 °C to +85 °C					
V_{IH}	HIGH-level input voltage	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V _{CC} = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	$0.3 \times V_{CC}$	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = 100 μ A; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		$I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	0.07	0.45	V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	0.12	0.3	V
		I_{O} = 12 mA; V_{CC} = 2.7 V	-	0.17	0.4	V
		$I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	0.33	0.55	V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.39	0.55	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -100~\mu A;~V_{CC} = 1.65~V~to~5.5~V$	$V_{CC}-0.1$	-	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	1.54	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	2.15	-	V
		$I_O = -12$ mA; $V_{CC} = 2.7$ V	2.2	2.50	-	V
		$I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.3	2.62	-	V
		$I_O = -32$ mA; $V_{CC} = 4.5$ V	3.8	4.11	-	V
I _I	input leakage current	$V_I = 5.5 \text{ V or GND}$; $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	±0.1	±5	μΑ
I _{OFF}	power-off leakage current	V_I or $V_O = 5.5 \text{ V}$; $V_{CC} = 0 \text{ V}$	-	±0.1	±10	μΑ
I _{CC}	supply current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}; I_O = 0 \text{ A}$	-	0.1	10	μΑ
Δl _{CC}	additional supply current	per pin; $V_I = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 2.3 \text{ V}$ to 5.5 V	-	5	500	μΑ
Cı	input capacitance		-	2.5	-	pF

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
T _{amb} = -	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V _{CC} = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	$0.3 \times V_{CC}$	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_{O} = 100 μ A; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		$I_O = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.70	V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.60	V
		$I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.80	V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.80	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -100 \mu A$; $V_{CC} = 1.65 V$ to 5.5 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	0.95	-	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.7	-	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	1.9	-	-	V
		$I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.0	-	-	V
		$I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.4	-	-	V
I _I	input leakage current	$V_I = 5.5 \text{ V or GND}$; $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	±20	μΑ
I _{OFF}	power-off leakage current	V_I or $V_O = 5.5 \text{ V}$; $V_{CC} = 0 \text{ V}$	-	-	±20	μΑ
I _{CC}	supply current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}; I_O = 0 \text{ A}$	-	-	40	μΑ
ΔI_{CC}	additional supply current	per pin; $V_1 = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 2.3 \text{ V}$ to 5.5 V	-	-	5000	μΑ

^[1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground 0 V); for test circuit see Figure 6.

Symbol	Parameter	Conditions		-40	°C to +85	°C	-40 °C to	+125 °C	Unit
				Min	Typ[1]	Max	Min	Max	
t _{pd}	propagation delay	nA, nB to nY; see Figure 5	[2]						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.4	3.8	9.9	1.4	12.4	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		8.0	2.5	5.7	8.0	7.2	ns
		$V_{CC} = 2.7 \text{ V}$		0.8	3.0	5.7	0.8	7.2	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		8.0	2.3	4.7	8.0	5.9	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.6	1.9	3.6	0.6	4.5	ns
C_{PD}	power dissipation capacitance	per gate; V_I = GND to V_{CC} ; V_{CC} = 3.3 V	[3]						
		output enabled		-	15.8	-	-	-	pF

- [1] Typical values are measured at $T_{amb} = 25$ °C and $V_{CC} = 1.8$ V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL}
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}{}^2 \times f_o) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

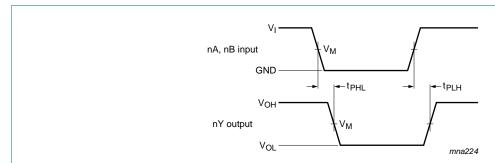
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



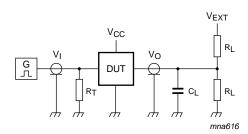
Measurement points are given in Table 9.

 V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. Propagation delay input (nA, nB) to output (nY)

Table 9. Measurement points

Supply voltage	Input	Output
V _{CC}	V _M	V _M
1.65 V to 1.95 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.3 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$



Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 6. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input		Load	Load			
V _{CC}	V _I	t _r , t _f	CL	R_L	t _{PLH} , t _{PHL}		
1.65 V to 1.95 V	V _{CC}	\leq 2.0 ns	30 pF	1 kΩ	open		
2.3 V to 2.7 V	V _{CC}	≤ 2.0 ns	30 pF	$500~\Omega$	open		
2.7 V	2.7 V	≤ 2.5 ns	50 pF	$500~\Omega$	open		
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500Ω	open		
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open		

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

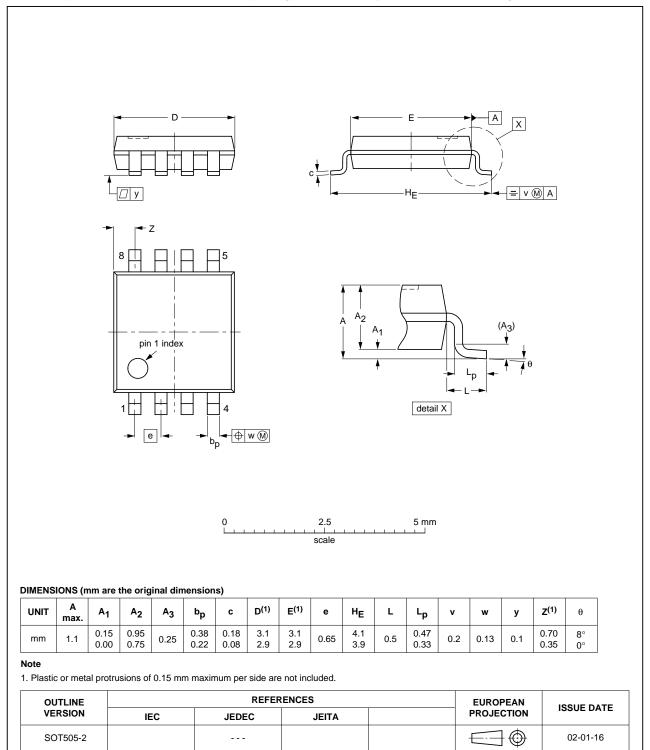
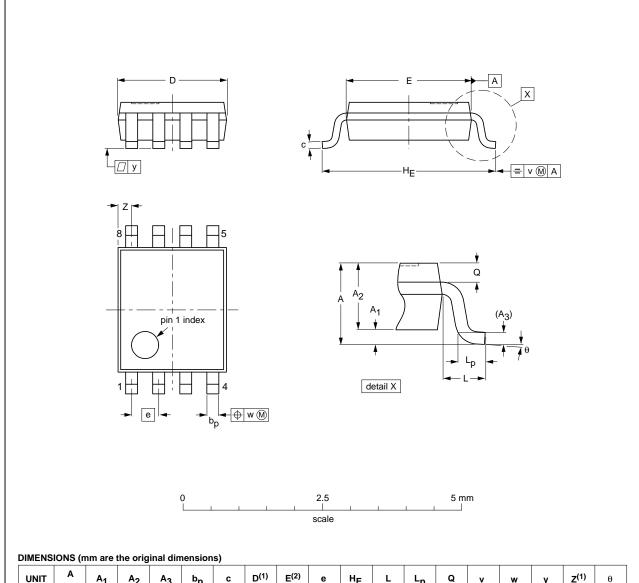


Fig 7. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A ₁	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	ď	٧	w	у	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT765-1		MO-187				02-06-07

Fig 8. Package outline SOT765-1 (VSSOP8)

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14. Abbreviations

Table 11. Abbreviations

Acronym	Description	
CMOS	Complementary Metal-Oxide Semiconductor	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
НВМ	Human Body Model	
MIL	Military	
MM	Machine Model	
TTL	Transistor-Transistor Logic	

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC2G86_Q100 v.1	20130507	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Dual 2-input EXCLUSIVE-OR gate

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